

INT100

Half-Bridge Driver IC

Low-Side and High-side Drive with Simultaneous Conduction Lockout



Product Highlights

5 V CMOS Compatible Control Inputs

- Combines logic inputs for low and high-side drives
- Schmidt-triggered inputs for noise immunity

Built-in High-voltage Level Shifters

- Can withstand up to 800 V for direct interface to the HV-referenced high-side switch
- Pulsed internal high-voltage level shifters reduce power consumption

Gate Drive Outputs for External MOSFETs

- Provides 300 mA sink/150 mA source current
- Can drive MOSFET gates at up to 15 V
- External MOSFET allows flexibility in design for various motor sizes

Built-in Protection Features

- Simultaneous conduction lockout protection
- Undervoltage lockout

Description

The INT100 half-bridge driver IC provides gate drive for external low-side and high-side MOSFET switches. The INT100 provides a simple, cost-effective interface between low-voltage control logic and high-voltage loads. The INT100 is designed to be used with rectified 110 V or 220 V supplies. Both high-side and low-side switches can be controlled independently from ground-referenced 5 V logic inputs.

Built-in protection logic prevents both switches from turning on at the same time and shorting the high voltage supply. Pulsed internal level shifting saves power and provides enhanced noise immunity. The circuit is powered from a nominal 15 V supply to provide adequate gate drive for external N-channel MOSFETs. A floating high-side supply is derived from the low-voltage rail by using a simple bootstrap technique.

Applications for the INT100 include motor drives, electronic ballasts, and uninterruptible power supplies. Multiple devices can also be used to implement full-bridge and multi-phase configurations.

The INT100 is available in a 16-pin plastic SOIC package.

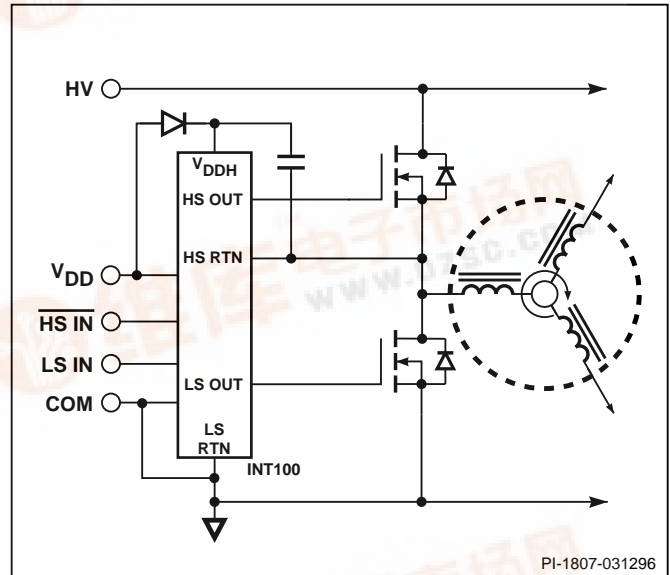


Figure 1. Typical Application

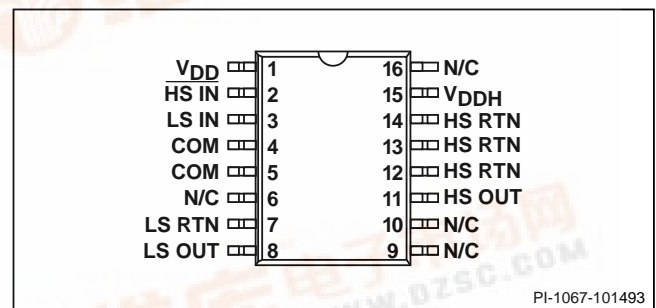


Figure 2. Pin Configuration.

ORDERING INFORMATION		
PART NUMBER	PACKAGE OUTLINE	ISOLATION VOLTAGE
INT100S	S16A	800 V



INT100

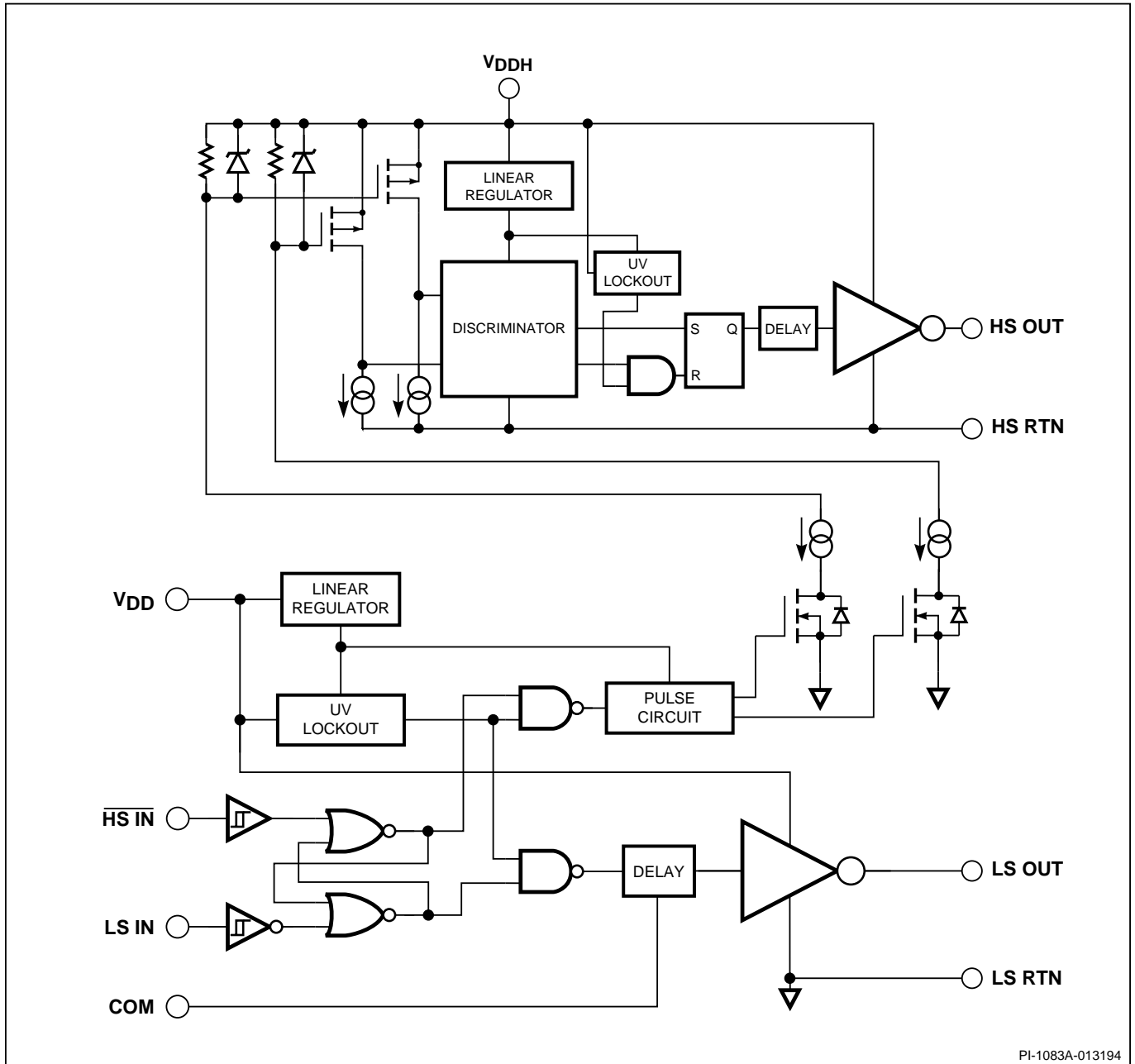


Figure 3. Functional Block Diagram of the INT100



Pin Functional Description

Pin 1:

V_{DD} supplies power to the logic, high-side interface, and low-side driver.

Pin 2:

Active-low logic level input $\overline{\text{HS IN}}$ controls the high-side driver output.

Pin 3:

Active-high logic level input **LS IN** controls the low-side driver output.

Pin 4, 5:

COM connection is used as the analog reference point for the circuit.

Pin 7:

LS RTN is the power reference point for the low-side circuitry, and should be connected to the source of the low-side MOSFET and to the COM pin.

Pin 8:

LS OUT is the driver output which controls the low-side MOSFET.

Pin 11:

HS OUT is the driver output which controls the high-side MOSFET.

Pin 12,13,14:

HS RTN is the power reference point for the high-side circuitry, and should be connected to the source of the high-side MOSFET.

Pin 15:

V_{DDH} supplies power to the high-side control logic and output driver. This is normally connected to a high-side referenced bootstrap circuit or can be supplied from a separate floating power supply.

INT100 Functional Description

5 V Regulators

Both low-side and high-side driver circuits incorporate a 5 V linear regulator circuit. The low-side regulator provides the supply voltage for the control logic and high-voltage level shift circuit. This allows $\overline{\text{HS IN}}$ and **LS IN** to be directly compatible with 5 V CMOS logic without the need of an external 5 V supply. The high-side regulator provides the supply voltage for the noise rejection circuitry and high-side control logic.

Undervoltage Lockout

The undervoltage lockout circuit for the low-side driver disables both the **LS OUT** and **HS OUT** pins whenever the V_{DD} power supply falls below typically 9.0 V, and maintains this condition until the V_{DD} power supply rises above typically 9.35 V. This guarantees that both MOSFETs will remain off during power-up or fault conditions.

The undervoltage lockout circuit for the high-side driver disables the **HS OUT** pin whenever the V_{DDH} power supply falls below typically 9.0 V, and maintains this condition until the V_{DDH} power supply rises above typically 9.35 V.

This guarantees that the high-side MOSFET will be off during power-up or fault conditions.

Level Shift

The level shift control circuitry of the low-side driver is connected to integrated high-voltage N-channel MOSFET transistors which perform the level-shifting function for communication to the high-side driver. Controlled current capability allows the drain voltage to float with the high-side driver. Two individual channels produce a true differential communication channel for accurately controlling the high-side driver in the presence of fast moving high-voltage waveforms. The high voltage level shift transistors employed exhibit very low output capacitance, minimizing the displacement currents between the low-side and high-side drivers during fast moving voltage transients created during switching of the external MOSFETs. As a result, power dissipation is minimized and noise immunity optimized.

The pulse circuit provides the two high-voltage level shifters with precise timing

signals. These signals are used by the discriminator to reject spurious noise. The combination of differential communication with the precise timing provides maximum immunity to noise.

Simultaneous Conduction Lockout

A latch prevents the low-side driver and high-side driver from being on at the same time, regardless of the input signals.

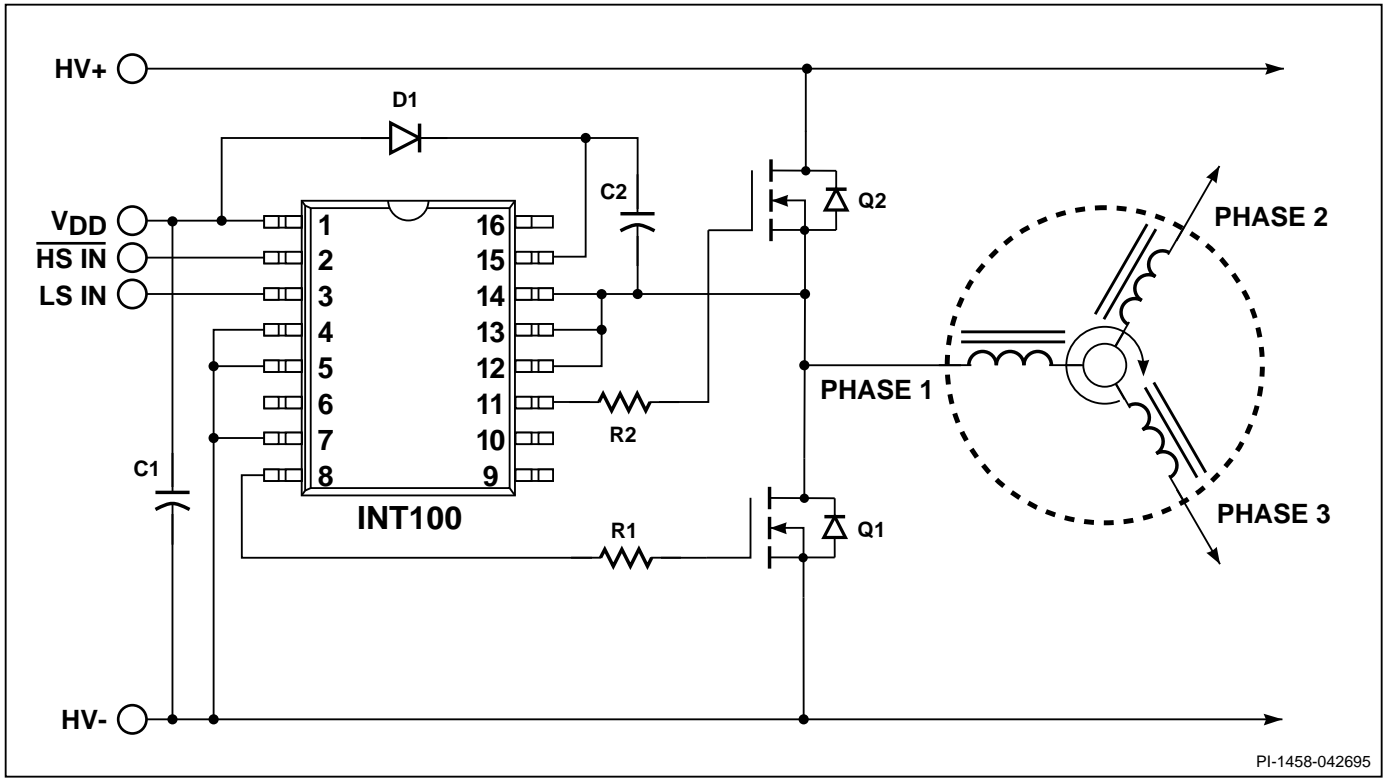
Delay Circuit

The delay circuit matches the low-side propagation delay with the combination of the pulse circuit, high voltage level shift, and high-side driver propagation delays. This ensures that the low-side driver and high-side driver will never be on at the same time during switching transitions in either direction.

Driver

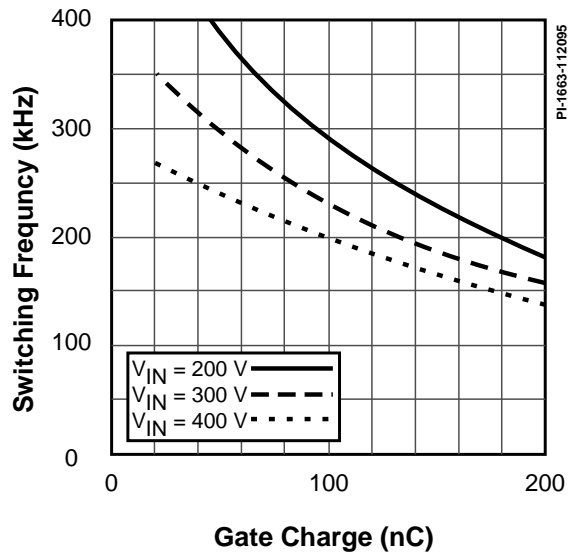
The CMOS drive circuitry on both low-side and high-side driver ICs provide drive power to the gates of the external MOSFETs. The drivers consist of a CMOS buffer capable of driving external transistor gates at up to 15 V.

INT100



PI-1458-042695

Figure 4. Using the INT100 in a 3-phase Configuration.



PI-1663-112095

Figure 5. Gate Charge versus Switching Frequency.

General Circuit Operation

One phase of a three-phase motor drive circuit is shown in Figure 4 to illustrate an application of the INT100. The LS IN signal directly controls MOSFET Q1. The HS IN signal controls MOSFET Q2 via the high voltage level shift transistors communicating with the high-side driver. The INT100 will ignore input signals that would command both Q1 and Q2 to conduct simultaneously, protecting against shorting the HV+ bus to HV-.

Local bypassing for the low-side driver is provided by C1. Bootstrap bias for the high-side driver is provided by D1 and C2. Slew rate and effects of parasitic oscillations in the load waveforms are controlled by resistors R1 and R2.

The inputs are designed to be compatible with 5 V CMOS logic levels and should not be connected to V_{DD} . Normal CMOS power supply sequencing should be

observed. The order of signal application should be V_{DD} , logic signals, and then HV+. V_{DD} should be supplied from a low impedance voltage source.

The output returns (HS RTN and LS RTN) are isolated from one another by the internal high-voltage MOSFET level shifters. The level shift circuitry is designed to operate properly even when the HS RTN swings as much as 5 V below the LS RTN pin with V_{DDH} biased at 15 V. The INT100 will also safely tolerate more negative voltages (as low as $-V_{DDH}$ below LS RTN).

Maximum frequency of operation is limited by power dissipation due to high-voltage switching, gate charge, and bias power. Figure 5 indicates the maximum switching frequency as a function of input voltage and gate charge. For higher ambient temperatures, the switching frequency should be derated linearly.

The bootstrap capacitor must be large enough to provide bias current over the entire on-time of the high-side driver without significant voltage sag or decay. The high-side MOSFET gate charge must also be supplied at the desired switching frequency. Figure 6 shows the maximum high-side on-time versus gate charge of the external MOSFET. Applications with extremely long high-side on-times require special techniques discussed in AN-10.

The high-side driver is latched on and off by the edges of the appropriate low-side logic signal. The high-side driver will latch off and stay off if the bootstrap capacitor discharges below the undervoltage lockout threshold. Undervoltage lockout-induced turn off can occur during conditions such as power ramp up, motor start, or low speed operation.

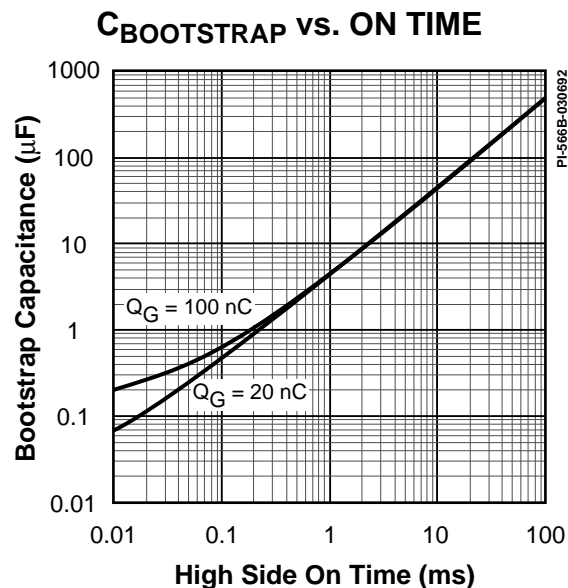


Figure 6. High-side On Time versus Bootstrap Capacitor.

ABSOLUTE MAXIMUM RATINGS¹

V _{DD} Voltage	16.5 V	Ambient Temperature	-40 to 85°C
V _{DDH} Voltage	HS RTN + 16.5 V	Junction Temperature	150°C
HS RTN	800 V - V _{DDH} to -V _{DDH}	Lead Temperature ⁽²⁾	260°C
HS RTN Slew Rate	10V/ns	Power Dissipation (T _A = 25°C)	2.3 W
Logic Input Voltage	-0.3V to 5.5 V	(T _A = 70°C)	1.5 W
LS OUT Voltage	LS RTN - 0.3 V to V _{DD} + 0.3 V	Thermal Impedance (θ _{JA})	55°C/W
HS OUT Voltage	HS RTN - 0.3 V to V _{DDH} + 0.3 V	1. Unless noted, all voltages referenced to COM, T _A = 25°C	
Storage Temperature	-65 to 125°C	2. 1/16" from case for 5 seconds.	

Parameter	Symbol	Conditions (Unless Otherwise Specified)		Min	Typ	Max	Units
		V _{DDH} = V _{DD} = 15 V HS RTN = LS RTN = COM = 0 V T _A = -40 to 85°C					
LOGIC							
Input Current, High or Low	I _{IH} , I _{IL}	V _{IH} = 4.0 V		0	10	150	μA
		V _{IL} = 1.0 V		-20	0	20	
Input Voltage High	V _{IH}			4.0			V
Input Voltage Low	V _{IL}					1.0	V
Input Voltage Hysteresis	V _{HY}			0.3	0.7		V
LS OUT/HS OUT							
Output Voltage High	V _{OH}	I _o = -20 mA	LS OUT	V _{DD} -1.0	V _{DD} -0.5		V
			HS OUT	V _{DDH} -1.0	V _{DDH} -0.5		
Output Voltage Low	V _{OL}	I _o = 40 mA			0.3	1.0	V
Output Short Circuit Current	I _{OS}	See Note 1	V _o = 0 V	-150			mA
			V _o = 15 V	300			
Turn-on Delay Time	t _{d(on)LS}	See Figure 7	LS OUT		0.6	1.0	μs
	t _{d(on)HS}		HS OUT		1.0	1.5	
Rise Time	t _r	See Figure 7			80	120	ns
Turn-off Delay Time	t _{d(off)LS}	See Figure 7	LS OUT		500	1000	ns
	t _{d(off)HS}		HS OUT		420	600	
Fall Time	t _f	See Figure 7			50	100	ns



Parameter	Symbol	Conditions	Min	Typ	Max	Units
		(Unless Otherwise Specified) $V_{DDH} = V_{DD} = 15\text{ V}$ $HS\ RTN = LS\ RTN = COM = 0\text{ V}$ $T_A = -40\text{ to }85^\circ\text{C}$				
LEVEL SHIFT						
Breakdown Voltage	BV_{DSS}	$V_{DDH} = HS\ OUT = HS\ RTN$ $I_{HS\ RTN} = 100\ \mu\text{A}$	800			V
Leakage Current	$I_{HS\ RTN}$	$V_{DDH} = HS\ OUT = HS\ RTN = 500\text{ V}$		0.2	30	μA
Interface Capacitance		$V_{DDH} = HS\ OUT = HS\ RTN = 500\text{ V}$		20		pF
SYSTEM RESPONSE						
Deadtime (Low Off to High On)	Dt_{P+}	See Figure 7	0	450		ns
Deadtime (High Off to Low On)	Dt_{P-}	See Figure 7	0	300		ns
UNDERVOLTAGE LOCKOUT						
Input UV Trip-off Voltage	$V_{DD(UV)}$ $V_{DDH(UV)}$		8.5	9.0	10	V
Input UV Hysteresis			175	350		mV
SUPPLY						
Supply Current	I_{DD}, I_{DDH}	See Note 2		1.5	3.0	mA
Supply Voltage	V_{DD}, V_{DDH}		10		16	V

NOTES:

- Applying a short circuit to the LS OUT or HS OUT pin for more than 500 μs will exceed the thermal rating of the package, resulting in destruction of the part.
- V_{DD}, V_{DDH} supply must have less than 30 Ω output impedance.

INT100

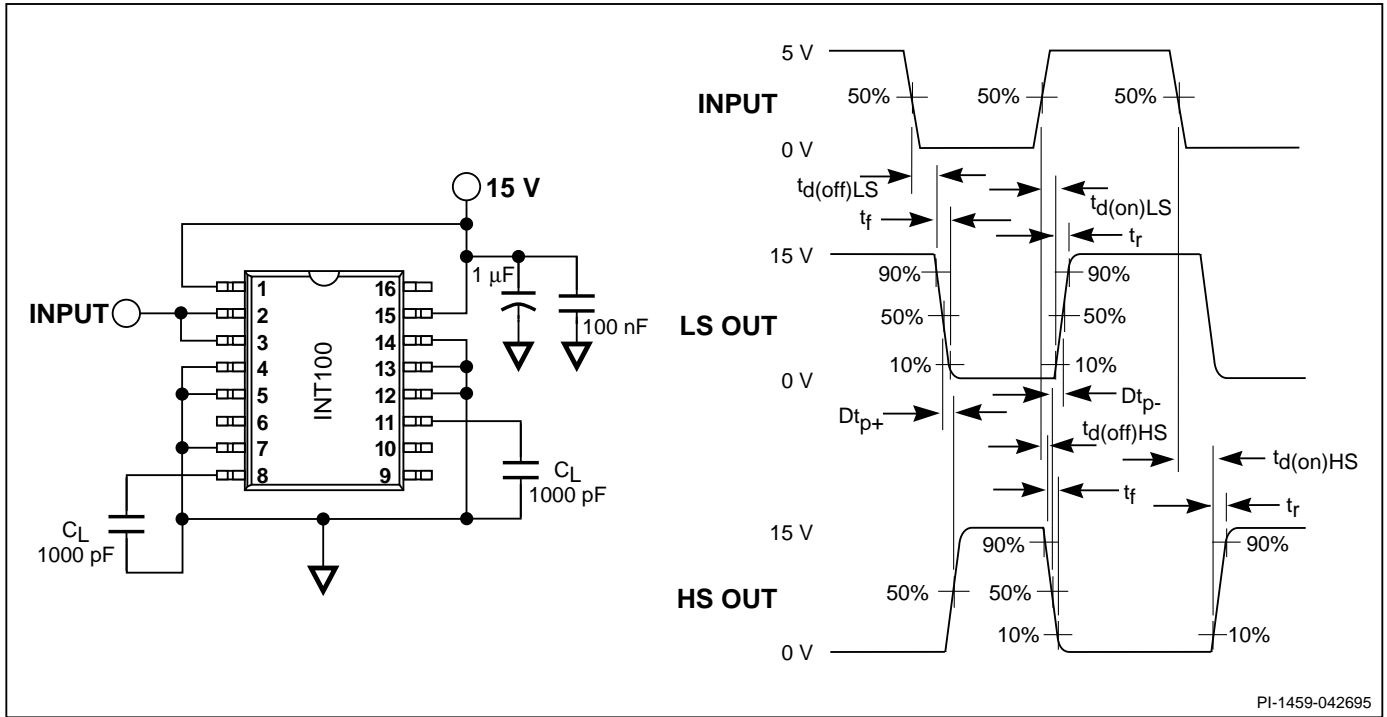
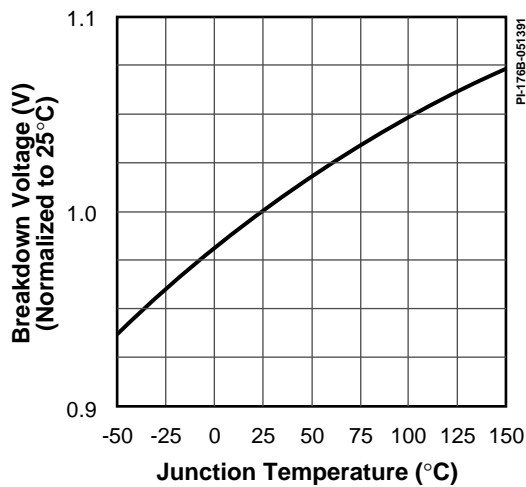
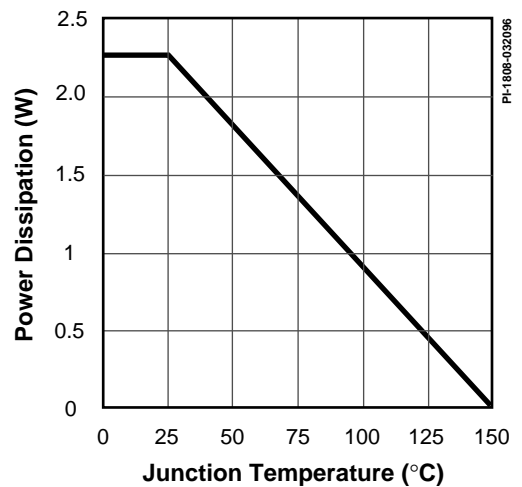


Figure 7. Switching Time/Deadtime Test Circuit.

BREAKDOWN vs. TEMPERATURE



PACKAGE POWER DERATING



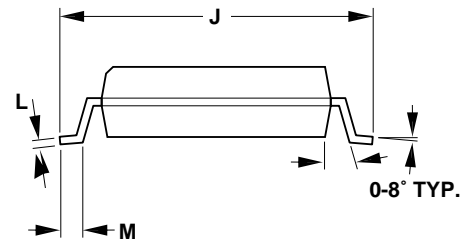
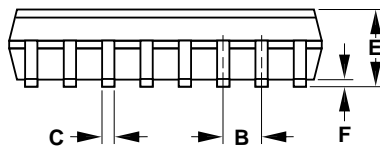
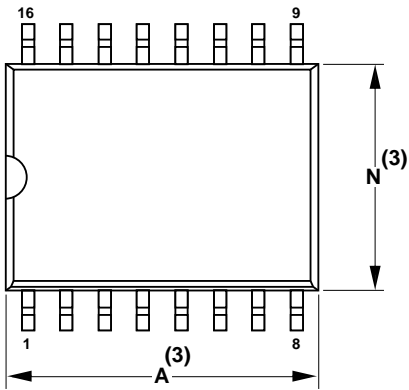
S16A

Plastic SO-16 (W)

DIM	inches	mm
A	.398-.413	10.10-10.50
B	.050 BSC	1.27 BSC
C	.014-.018	0.36-0.46
E	.093-.104	2.35-2.65
F	.004-.012	0.10-0.30
J	.394-.418	10.01-10.62
L	.009-.012	0.23-0.32
M	.020-.040	0.51-1.02
N	.291-.299	7.40-7.60

Notes:

1. Package dimensions conform to JEDEC specification MS-013-AA for standard small outline (SO) package, 16 leads, 7.50 mm (.300 inch) body width (issue A, June 1985).
2. Controlling dimensions are in mm.
3. Dimensions are for the molded body and do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .15 mm (.006 inch) on any side.
4. Pin 1 side identified by chamfer on top edge of the package body or indent on Pin 1 end.



PI-1846-050196



Notes



Notes

Power Integrations reserves the right to make changes to its products at any time to improve reliability or manufacturability. Power Integrations does not assume any liability arising from the use of any device or circuit described herein, nor does it convey any license under its patent rights or the rights of others.

PI Logo and **TOPSwitch** are registered trademarks of Power Integrations, Inc.
©Copyright 1994, Power Integrations, Inc. 477 N. Mathilda Avenue, Sunnyvale, CA 94086

WORLD HEADQUARTERS

Power Integrations, Inc.
477 N. Mathilda Avenue
Sunnyvale, CA 94086
USA
Main: 408•523•9200
Customer Service:
Phone: 408•523•9265
Fax: 408•523•9365

AMERICAS

For Your Nearest Sales/Rep Office
Please Contact Customer Service
Phone: 408•523•9265
Fax: 408•523•9365

EUROPE & AFRICA

Power Integrations (Europe) Ltd.
Mountbatten House
Fairacres
Windsor SL4 4LE
United Kingdom
Phone: 44•(0)•1753•622•208
Fax: 44•(0)•1753•622•209

JAPAN

Power Integrations, K.K.
Keihin-Tatemono 1st Bldg.
12-20 Shin-Yokohoma 2-Chome, Kohoku-ku
Yokohama-shi, Kanagawa 222 Japan
Phone: 81•(0)•45•471•1021
Fax: 81•(0)•45•471•3717

ASIA & OCEANIA

For Your Nearest Sales/Rep Office
Please Contact Customer Service
Phone: 408•523•9265
Fax: 408•523•9365

APPLICATIONS HOTLINE

World Wide 408•523•9260

APPLICATIONS FAX

Americas 408•523•9361
Europe/Africa
44•(0)•1753•622•209
Japan 81•(0)•45•471•3717
Asia/Oceania 408•523•9364

